

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **BLY92C** is Designed for
Class C FM Amplifier Applications
up to 250 MHz.

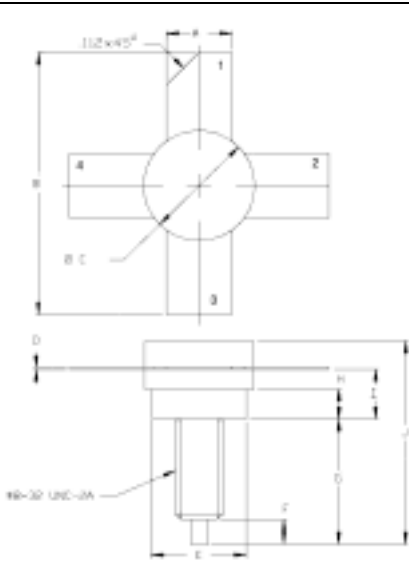
FEATURES:

- $P_G = 11$ dB Typical at 175 MHz
- High Load VSWR Capability
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	4.0 A
V_{CB}	65 V
V_{CE}	35 V
V_{EB}	4.0 V
P_{DISS}	40 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	4.4 $^\circ\text{C/W}$

PACKAGE STYLE .380" 4L STUD

		MINIMUM Inches/mm	MAXIMUM Inches/mm
A		220/5,59	.230/5,84
B		980/24,89	
C		370/9,40	.385/9,78
D		004/0,10	.007/0,18
E		320/8,13	.330/8,38
F		100/2,54	.130/3,30
G		450/11,43	490/12,45
H		.090/2,29	.100/2,54
I		.155/3,94	.175/4,45
J			.750/19,05

1 = COLLECTOR 2 & 4 = EMITTER
3 = BASE

ORDER CODE: ASI10758

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	$I_C = 200$ mA	65			V
BV_{CEO}	$I_C = 200$ mA	35			V
BV_{EBO}	$I_E = 10$ mA	4.0			V
I_{CBO}	$V_{CB} = 30$ V			2.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 200$ mA	35			---
C_{ob}	$V_{CB} = 30$ V $f = 1.0$ MHz		40	50	pF
P_G η_c	$V_{CC} = 28$ V $P_{OUT} = 15$ W $f = 175$ MHz	10 50	11 60		dB %